

1 1. (Amended) A die seal structure for a semiconductor die having a
2 substrate comprising:
3 an elongate region electrically isolated from the remainder of the substrate
4 extending around a major portion of the periphery of the substrate and having a gap
5 between ends of the elongate region along a minor portion of the periphery; and
6 a conductive seal ring extending around the entire periphery of the die in
7 direct contact with the die throughout said elongate region in direct contact with and said
8 gap to provide a limited electrical connection between the ring and the substrate at said
9 gap.

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2 14. (Amended) A die seal structure for a semiconductor die having a
3 substrate of a first conductivity type, comprising:
4 an elongate well region of a second conductivity type opposite from the
5 first conductivity type extending around a major portion of the periphery of the substrate
6 and having a gap between the ends of the elongate region along a minor portion of the
7 periphery; and
8 a conductive seal ring extending around the entire periphery of the die in
9 direct contact with the die throughout said elongate well region and in said gap to provide
10 a limited electrical connection between the ring and the substrate of said first
11 conductivity type at said gap.

1 18. (Amended) A semiconductor device comprising:
2 a. a die including a substrate;
3 b. a die seal structure on the substrate, the structure comprising:
4 an elongate region electrically isolated from the remainder of the
5 substrate extending around a major portion of the periphery of the substrate and having a
6 gap between ends of the elongate region along a minor portion of the periphery; and